

# (12) International Application Status Report

**Received at International Bureau:** 25 December 2019 (25.12.2019)

**Information valid as of:** 28 May 2020 (28.05.2020)

**Report generated on:** 21 September 2020 (21.09.2020)

**(10) Publication number:**

WO2020/129884

**(43) Publication date:**

25 June 2020 (25.06.2020)

**(26) Publication language:**

Japanese (JA)

**(21) Application Number:**

PCT/JP2019/049131

**(22) Filing Date:**

16 December 2019 (16.12.2019)

**(25) Filing language:**

Japanese (JA)

**(31) Priority number(s):**

2018-236125 (JP)

**(31) Priority date(s):**

18 December 2018 (18.12.2018)

**(31) Priority status:**

Priority document received (in compliance with PCT Rule 17.1)

**(51) International Patent Classification:**

G01K 7/00 (2006.01); G01K 7/01 (2006.01)

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**(54) Title (EN):** TEMPERATURE DETECTION CIRCUIT

**(54) Title (FR):** CIRCUIT DE DÉTECTION DE TEMPÉRATURE

**(54) Title (JA):** 温度検出回路

**(57) Abstract:**

**(EN):** A temperature detection circuit (1) comprises: a bipolar first transistor (Q1); and a bipolar second transistor (Q2). The first transistor (Q1) and the second transistor (Q2) form a current mirror circuit (10). The temperature of an amplification circuit (30) is detected on the basis of changes in the temperatures of the first transistor (Q1) and the second transistor (Q2).

**(FR):** L'invention concerne un circuit de détection de température (1) comprenant : un premier transistor bipolaire (Q1) ; et un second transistor bipolaire (Q2). Le premier transistor (Q1) et le second transistor (Q2) forment un circuit miroir de courant (10). La température d'un circuit d'amplification (30) est détectée en fonction de changements des températures du premier transistor (Q1) et du second transistor (Q2).

**(JA):** 温度検出回路(1)は、バイポーラ型の第1トランジスタ(Q1)と、バイポーラ型の第2トランジスタ(Q2)と、を備え、第1トランジスタ(Q1)及び第2トランジスタ(Q2)はカレントミラー回路(10)を構成し、第1トランジスタ(Q1)及び第2トランジスタ(Q2)の温度変化に基づいて増幅回路(30)の温度を検出する。

**International search report:**

Received at International Bureau: 02 March 2020 (02.03.2020) [JP]

**International Report on Patentability (IPRP) Chapter II of the PCT:**

Not available

**(81) Designated States:**

AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW

European Patent Office (EPO) : AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR

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Eurasian Patent Organization (EAPO) : AM, AZ, BY, KG, KZ, RU, TJ, TM